# DB101S THRU DB107S

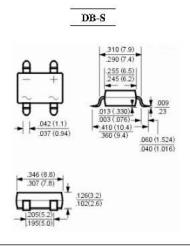
## SINGLE-PHASE GLASS PASSIVATED SILICON SURFACE MOUNT BRIDGE RECTIFIER Reverse Voltage - 50 to 1000 V Forward Current - 1 A

## Features

- High surge overload rating of 50 A peak
- Ideal for printed circuit board
- Low forward voltage drop
- · Glass passivated chip junction

#### **Mechanical Data**

- Case: Molded plastic, DB-S
- Epoxy: UL 94V-0 rate flame retardant
- Terminal: Leads solderable per MIL-STD-202, method 208 guaranteed
- Mounting position: Any



Dimensions in inches and (millimeters)

#### Maximum Ratings and Electrical Characteristics

Ratings at 25 °C ambient temperature unless otherwise specified. Single phase, half wave, 60Hz, resistive or inductive load. For capacitive load, derate current by 20%.

Parameter	Symbols	DB101S	DB102S	DB103S	DB104S	DB105S	DB106S	DB107S	Units
Maximum Recurrent Peak Reverse Voltage	$V_{RRM}$	50	100	200	400	600	800	1000	V
Maximum RMS Voltage	$V_{\text{RMS}}$	35	70	140	280	420	560	700	V
Maximum DC Blocking Voltage	V <sub>DC</sub>	50	100	200	400	600	800	1000	V
Maximum Average Forward Rectified Current at $T_A = 40 \text{ °C}^{-2}$	I <sub>(AV)</sub>	1							А
Peak Forward Surge Current 8.3 ms Single Half-sine -wave Superimposed on Rated Load (JEDEC Method)	I <sub>FSM</sub>	50						А	
Maximum Forward Voltage at 1 A DC	V <sub>F</sub>				1.1				V
Maximum Reverse Current $T_A = 25 \ ^{\circ}C$ at Rated DC Blocking Voltage $T_A = 125 \ ^{\circ}C$	I <sub>R</sub>	5 500							μΑ
Typical Junction Capacitance <sup>1)</sup>	CJ	25							pF
Typical Thermal Resistance 2)	$R_{\theta JA}$	40							°C/W
Typical Thermal Resistance 2)	$R_{\theta JL}$	15							°C/W
Operating and Storage Temperature Range	T <sub>j</sub> , T <sub>stg</sub>	- 55 to + 150							°C

<sup>1)</sup> Measured at 1 MHz and applied reverse voltage of 4 V DC.

 $^{\rm 2)}$  Units mounted P.C.B. with 0.5 X 0.5" (13 X 13 mm) copper pads.



